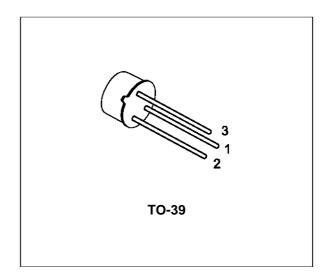


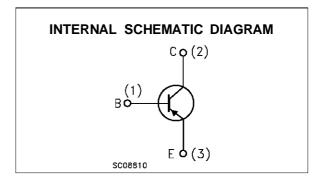
GENERAL PURPOSE TRANSISTORS

DESCRIPTION

The BC161 is a silicon planar epitaxial PNP transistors in Jedec TO-39 metal case. They are particularly designed for audio amplifiers and switching application up to 1A.

The complementary NPN type is the BC141.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		
V _{CBO}	Collector-Base Voltage (I _E = 0)	-60	V	
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	-60	V	
V_{EBO}	Emitter-Base Voltage (I _C = 0)	-5	V	
Ic	Collector Current	-1	Α	
lΒ	Base Current	-0.1	А	
P _{tot}	Total Dissipation at T _{amb} ≤ 45 °C	0.65	W	
	at T _{case} ≤ 45 °C	3.7	W	
T_{stg}	Storage Temperature	-55 to 175	°C	
Tj	Max. Operating Junction Temperature	175	°C	

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THERMAL DATA

ſ	R _{thj-case}	Thermal	Resistance	Junction-Case	Max	35	°C/W
	$R_{thj-amb}$	Thermal	Resistance	Junction-Ambient	Max	200	°C/W

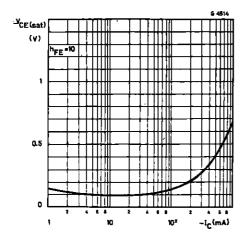
ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = -60 V V _{CE} = -60 V T _{amb} = 150 °C			-100 -100	nA μA
V _{(BR)CBO} *	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA	-60			V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -10 mA	-60			V
V _{(BR)EBO} *	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -100 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{C} = -100 \text{ mA}$ $I_{B} = -10 \text{ mA}$ $I_{C} = -500 \text{ mA}$ $I_{B} = -50 \text{ mA}$ $I_{B} = -100 \text{ mA}$		-0.1 -0.35 -0.6	-1	V V V
V _{BE(on)} *	Base-Emitter On Voltage	Ic = -1 A V _{CE} = -1 V		-1	-1.7	V
h _{FE} *	DC Current Gain	Ic = -100 μ A V_{CE} = -1 V for BC161 for BC161 Gr. 6 for BC161 Gr. 10 for BC161 Gr. 16 Ic = -100 mA V_{CE} = -1 V for BC161 for BC161 Gr. 6 for BC161 Gr. 10 for BC161 Gr. 16 Ic = -1 A V_{CE} = -1 V for BC161 for BC161 Gr. 10	40 40 63 100	110 46 80 120 140 63 100 160 26 15 20 30	250 100 160 250	
f⊤	Transition Frequency	$I_{C} = -50 \text{ mA}$ $V_{CE} = -10 \text{ V}$	50			MHz
Ссво	Collector Base Capacitance	$I_E = 0$ $V_{CB} = -20 \text{ V}$ $f = 1\text{MHz}$		15	30	pF
СЕВО	Emitter Base Capacitance	$I_C = 0$ $V_{CB} = -0.5 \text{ V}$ $f = 1\text{MHz}$			180	pF
ton	Turn-on Time	$I_{C} = -100 \text{ mA}$ $I_{B1} = -5 \text{ mA}$			500	ns
t_{off}	Turn-off Time	$I_C = -100 \text{ mA}$ $I_{B1} = I_{B2} = -5 \text{ mA}$			650	ns

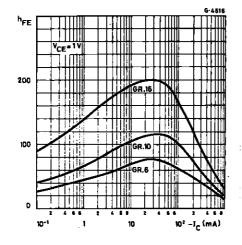
^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1 %



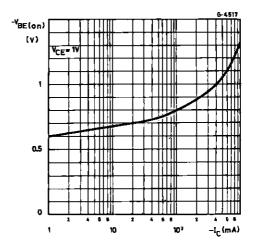
Collector-emitter Saturation Voltage.



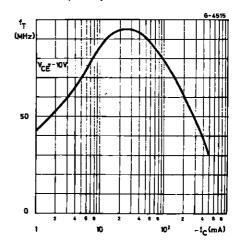
DC Current Gain.



Base-emitter Voltage.

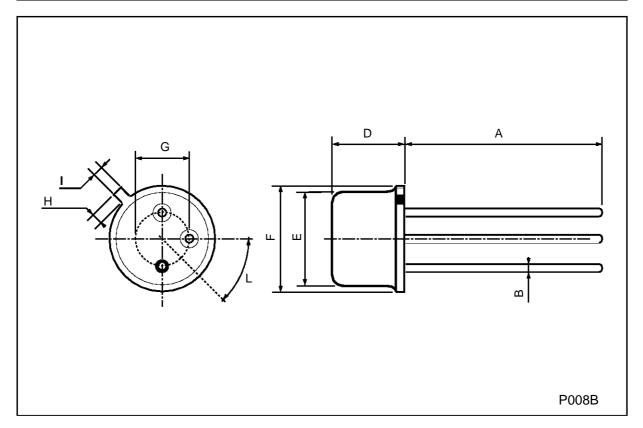


Transition Frequency.



TO-39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	12.7			0.500		
В			0.49			0.019
D			6.6			0.260
Е			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
Н			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



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